

FEATURES

- Low $V_{CE(sat)}$ Device
- 10 μ s Short Circuit Withstand
- High Thermal Cycling Capability
- High Current Density Enhanced DMOS SPT
- Isolated AISiC Base with AlN Substrates

APPLICATIONS

- Choppers
- Motor Controllers
- Power Supplies
- Traction Auxiliaries

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM250PKM33-TL000 is a Low $V_{CE(sat)}$ 3300V, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) chopper module configured with the upper arm of the bridge controlled. The IGBT has a wide reverse bias safe operating area (RBSOA). This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM250PKM33-TL000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}	3300V
$V_{CE(sat)}$ * (typ)	2.0V
I_C (max)	250A
$I_{C(PK)}$ (max)	500A

* Measured at the auxiliary terminals

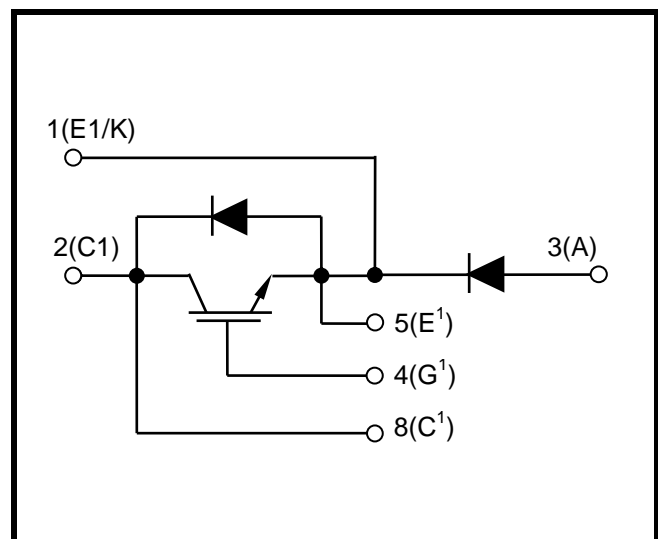
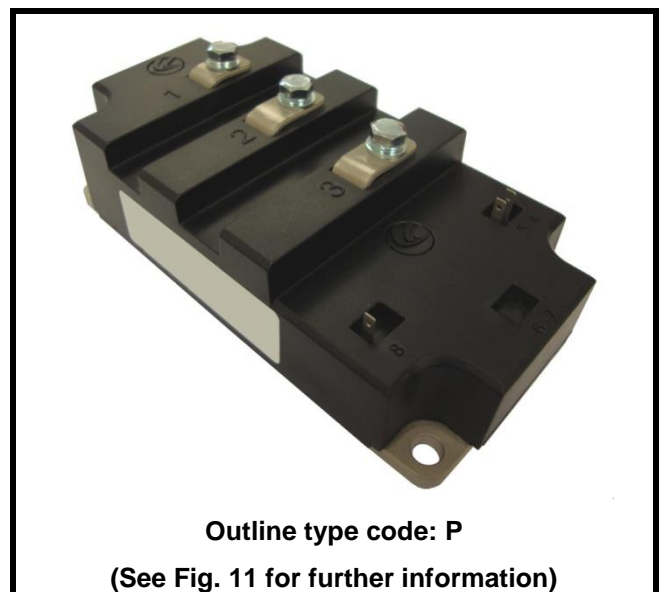


Fig. 1 Circuit configuration



Outline type code: P

(See Fig. 11 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{GE} = 0\text{V}$	3300	V
V_{GES}	Gate-emitter voltage		± 20	V
I_C	Continuous collector current	$T_{case} = 115^{\circ}\text{C}$	250	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 140^{\circ}\text{C}$	500	A
P_{max}	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$	2.6	kW
I^2t	Diode I^2t value – IGBT Arm	$V_R = 0$, $t_p = 10\text{ms}$, $T_j = 150^{\circ}\text{C}$	20	kA^2s
	Diode I^2t value – Diode Arm		20	kA^2s
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6000	V
Q_{PD}	Partial discharge – per module	IEC1287, $V_1 = 3500\text{V}$, $V_2 = 2600\text{V}$, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material:	AlN
Baseplate material:	AlSiC
Creepage distance:	33mm
Clearance:	20mm
CTI (Comparative Tracking Index):	>600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor	Continuous dissipation - junction to case	-	-	48	$^{\circ}\text{C}/\text{kW}$
$R_{th(j-c)}$	Thermal resistance – diode (IGBT Arm)	Continuous dissipation - junction to case	-	-	96	$^{\circ}\text{C}/\text{kW}$
	Thermal resistance – diode (Diode Arm)		-	-	96	$^{\circ}\text{C}/\text{kW}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	16	$^{\circ}\text{C}/\text{kW}$
T_j	Junction temperature	Transistor	-	-	150	$^{\circ}\text{C}$
		Diode	-	-	150	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-	-40	-	125	$^{\circ}\text{C}$
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M5	-	-	4	Nm

ELECTRICAL CHARACTERISTICS
T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I _{CES}	Collector cut-off current	V _{GE} = 0V, V _{CE} = V _{CES}			1	mA
		V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 125°C			15	mA
		V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 150°C			25	mA
I _{GES}	Gate leakage current	V _{GE} = ± 20V, V _{CE} = 0V			1	μA
V _{GE(TH)}	Gate threshold voltage	I _C = 20mA, V _{GE} = V _{CE}		5.7		V
V _{CE(sat)} †	Collector-emitter saturation voltage	V _{GE} = 15V, I _C = 250A		2.0		V
		V _{GE} = 15V, I _C = 250A, T _j = 125°C		2.6		V
		V _{GE} = 15V, I _C = 250A, T _j = 150°C		2.8		V
I _F	Diode forward current	DC		250		A
I _{FM}	Diode maximum forward current	t _p = 1ms		500		A
V _F	Diode forward voltage † (IGBT arm)	I _F = 250A		2.4		V
	Diode forward voltage ‡ (Diode arm)			2.5		V
	Diode forward voltage † (IGBT arm)	I _F = 250A, T _j = 125°C		2.5		V
	Diode forward voltage ‡ (Diode arm)			2.6		V
	Diode forward voltage † (IGBT arm)	I _F = 250A, T _j = 150°C		2.4		V
	Diode forward voltage ‡ (Diode arm)			2.5		V
C _{ies}	Input capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		45		nF
Q _g	Gate charge	±15V Including external C _{ge}		5		μC
C _{res}	Reverse transfer capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		1		nF
L _M	Module inductance			40		nH
R _{INT}	Internal transistor resistance			500		μΩ
SC _{Data}	Short circuit current, I _{SC}	T _j = 150°C, V _{CC} = 2500V t _p ≤ 10μs, V _{GE} ≤ 15V V _{CE(max)} = V _{CES} - L* x di/dt IEC 60747-9		950		A

Note:

† Measured at the auxiliary terminals

‡ Measured at the power busbars

 * L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

 $T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	$I_C = 250\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $R_{g(ON)} = 10\Omega$ $R_{g(OFF)} = 10\Omega$ $C_{GE} = 56\text{nF}$ $L_S \sim 150\text{nH}$		2700		ns
t_f	Fall time			610		ns
E_{OFF}	Turn-off energy loss			650		mJ
$t_{d(on)}$	Turn-on delay time			960		ns
t_r	Rise time			430		ns
E_{ON}	Turn-on energy loss			400		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 250\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 700\text{A}/\mu\text{s}$		140		μC
I_{rr}	Diode reverse recovery current			150		A
E_{rec}	Diode reverse recovery energy			170		mJ

 $T_{case} = 125^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	$I_C = 250\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $R_{g(ON)} = 10\Omega$ $R_{g(OFF)} = 10\Omega$ $C_{GE} = 56\text{nF}$ $L_S \sim 150\text{nH}$		2750		ns
t_f	Fall time			590		ns
E_{OFF}	Turn-off energy loss			680		mJ
$t_{d(on)}$	Turn-on delay time			1000		ns
t_r	Rise time			460		ns
E_{ON}	Turn-on energy loss			520		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 250\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 700\text{A}/\mu\text{s}$		230		μC
I_{rr}	Diode reverse recovery current			190		A
E_{rec}	Diode reverse recovery energy			280		mJ

 $T_{case} = 150^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	$I_C = 250\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $R_{g(ON)} = 10\Omega$ $R_{g(OFF)} = 10\Omega$ $C_{GE} = 56\text{nF}$ $L_S \sim 150\text{nH}$		2760		ns
t_f	Fall time			590		ns
E_{OFF}	Turn-off energy loss			750		mJ
$t_{d(on)}$	Turn-on delay time			940		ns
t_r	Rise time			460		ns
E_{ON}	Turn-on energy loss			550		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 250\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 700\text{A}/\mu\text{s}$		270		μC
I_{rr}	Diode reverse recovery current			200		A
E_{rec}	Diode reverse recovery energy			330		mJ

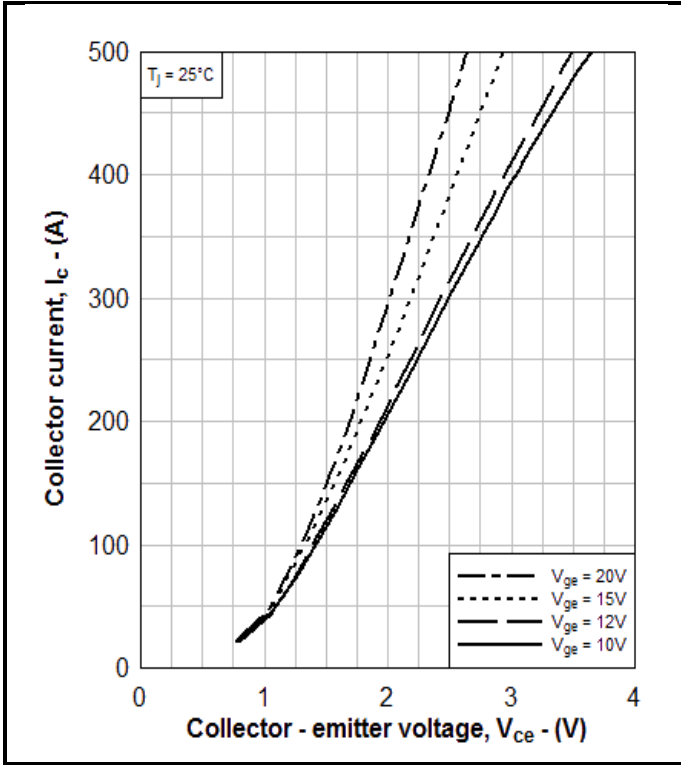


Fig. 3 Typical output characteristics

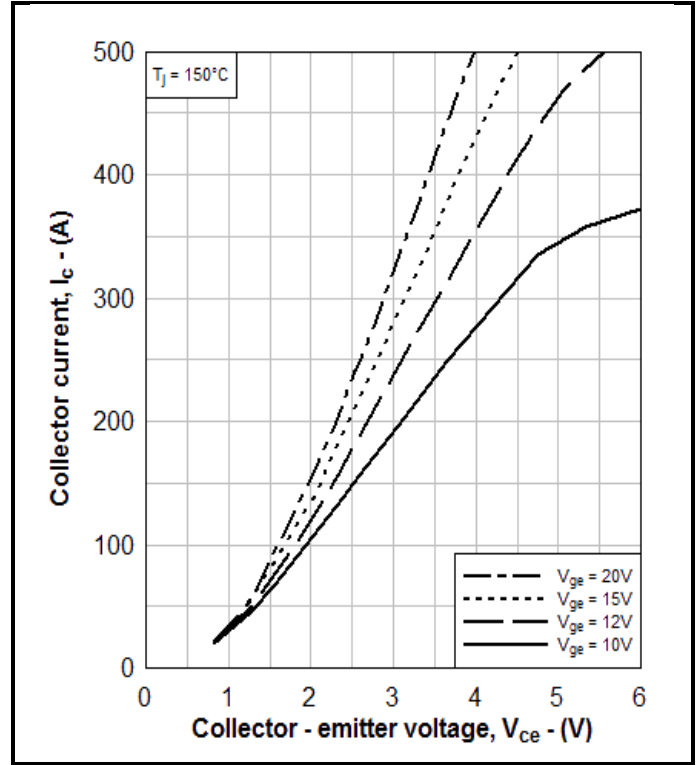


Fig. 4 Typical output characteristics

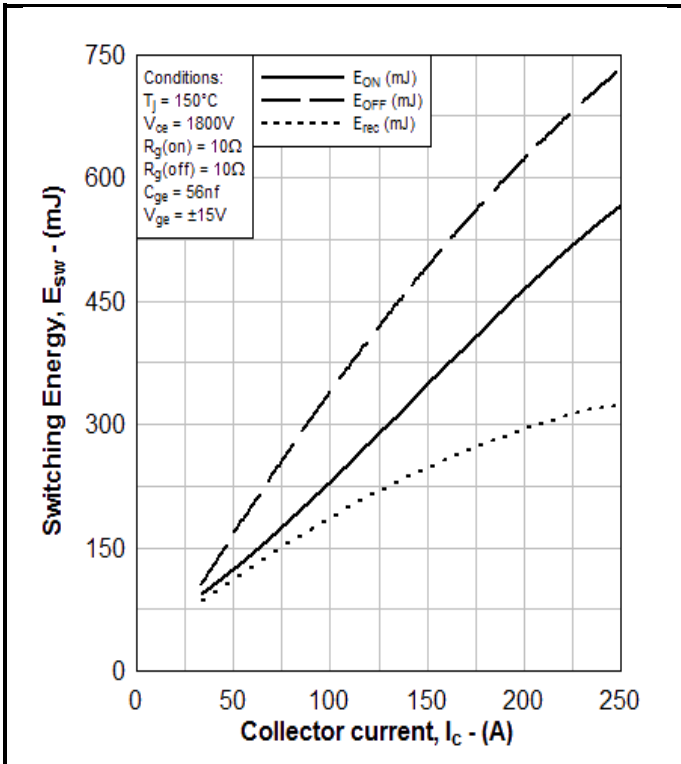


Fig. 5 Typical switching energy vs collector current

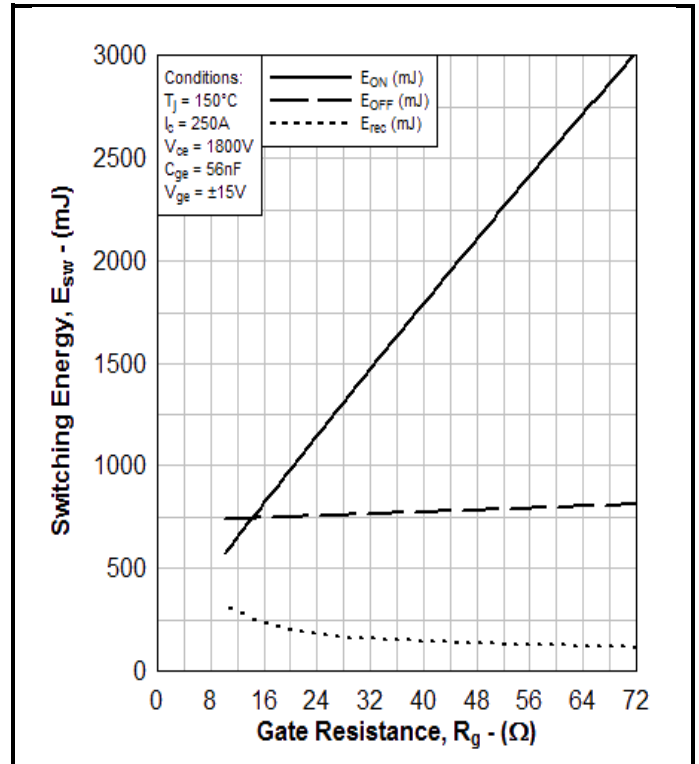


Fig. 6 Typical switching energy vs gate resistance

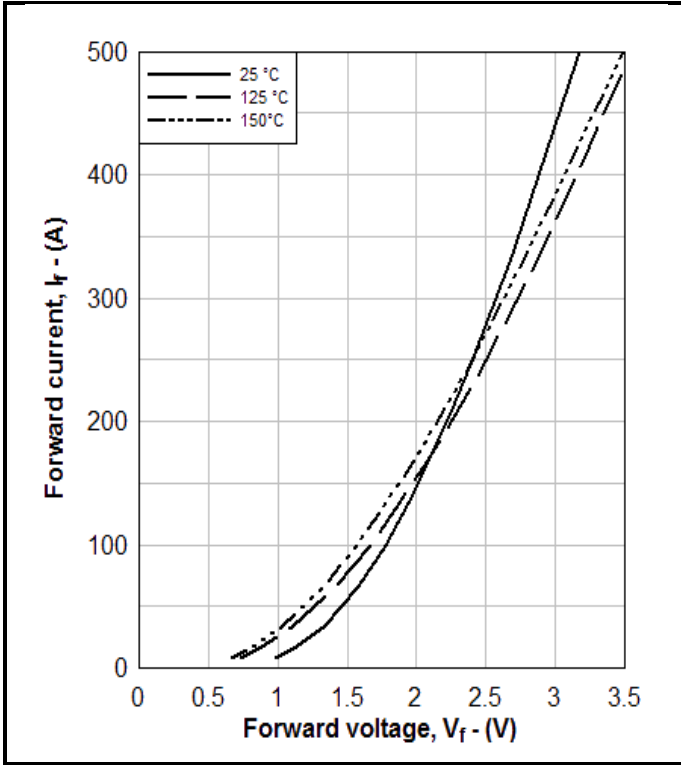


Fig. 7 Diode typical forward characteristics

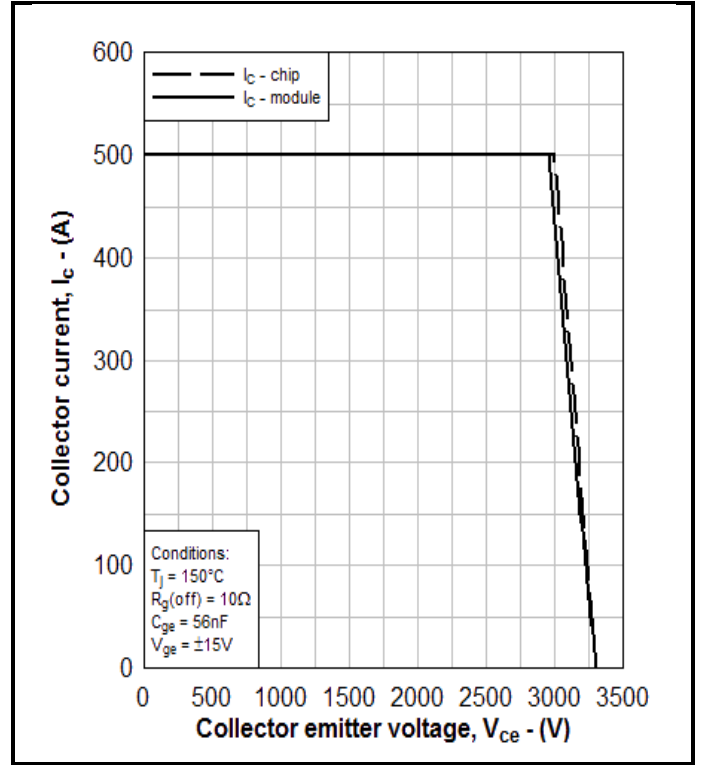


Fig. 8 Reverse bias safe operating area

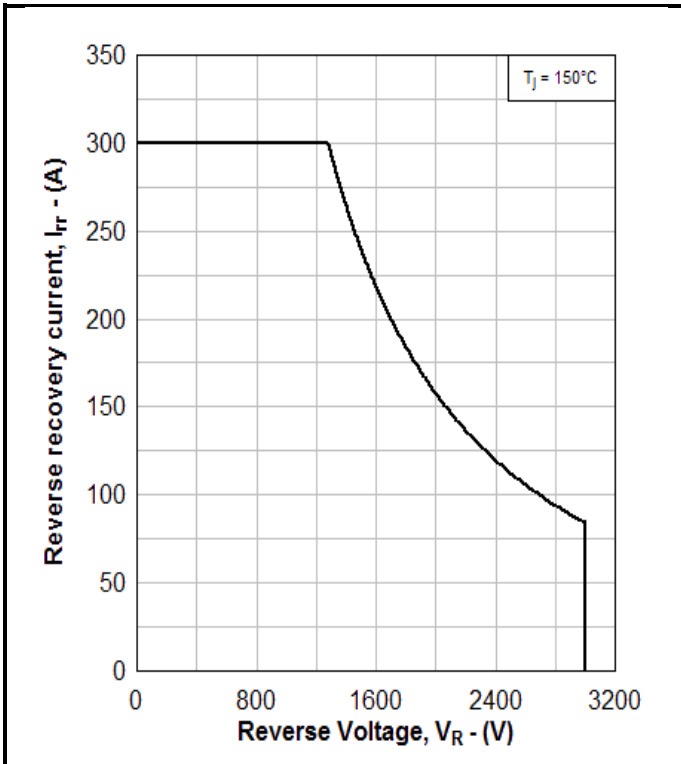


Fig. 9 Diode reverse bias safe operating area

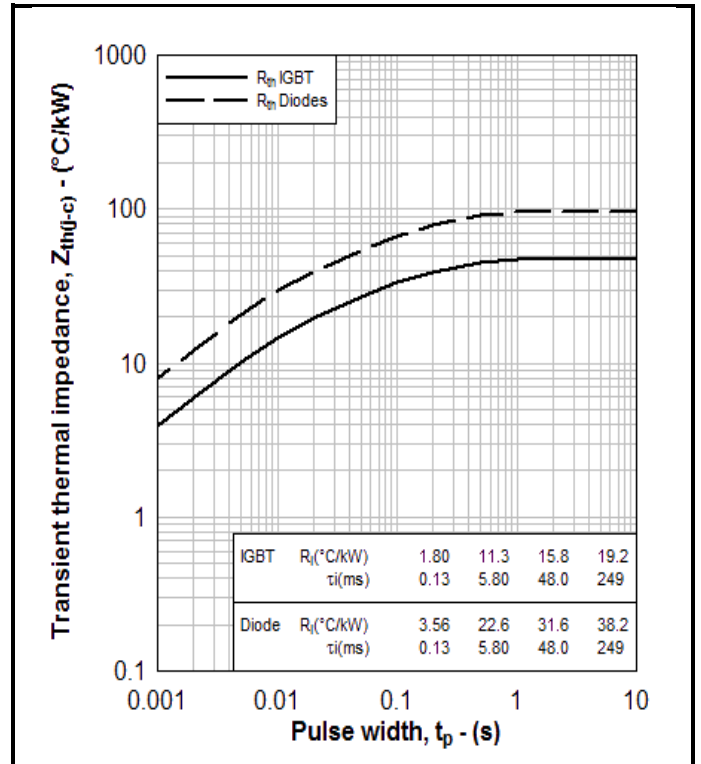
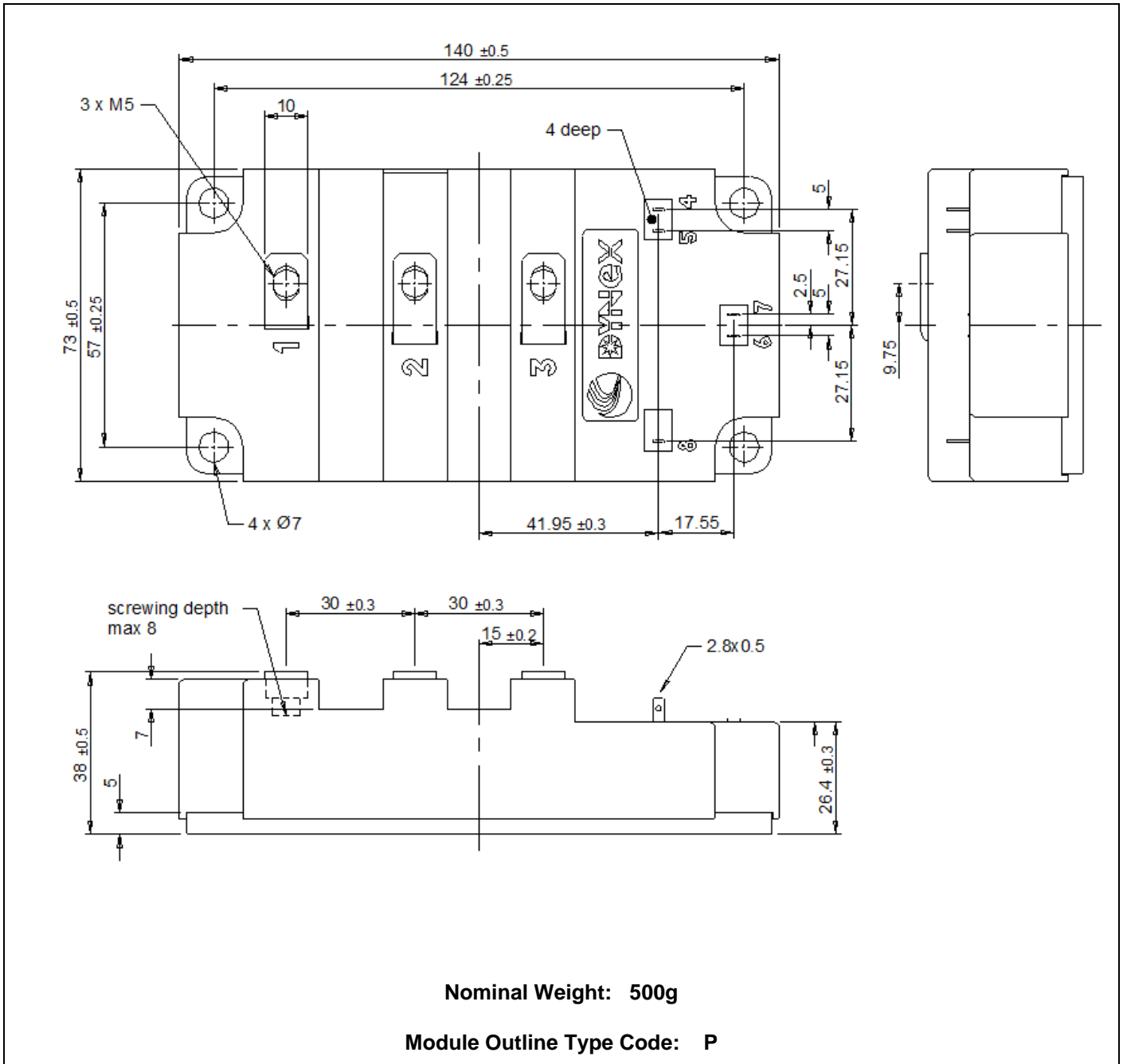


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
 All dimensions in mm, unless stated otherwise.
DO NOT SCALE.


Fig. 11 Module outline drawing

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